In the claims:

Please substitute the following full listing of claims for the claims as originally filed or most recently amended.

1. (Currently Amended) A field effect transistor formed at a surface of a layer of semiconductor material, said field effect transistor comprising

a gate structure formed on said surface of said layer of semiconductor material, and

a discontinuous film of material within said layer of semiconductor material and having a discontinuity aligned to said gate structure wherein said discontinuous film is a stressed film.

2. (Previously Presented) A field effect transistor as recited in claim 1, wherein said discontinuity is self-aligned to said gate structure.

3. (Canceled)

4. (Currently Amended) A field effect transistor as recited in claim ~~3~~ 1, wherein said stressed film comprises an insulator.

5. (Canceled)

6. (Currently Amended) ~~A field effect transistor as recited in claim 1,~~ A field effect transistor formed at a surface of a layer of semiconductor material, said field effect transistor comprising

a gate structure formed on said surface of said layer of semiconductor material, and

a discontinuous film of material within said layer of semiconductor material and having a discontinuity aligned to said gate structure wherein said discontinuous film has a stepped or staircase profile in cross-section.

7. (Currently Amended) A field effect transistor as recited in claim ~~3~~ 1, wherein said stressed film has a stepped or staircase profile in cross-section.

8. (Original) A field effect transistor as recited in claim 7 wherein said stepped or staircase portion defines an effective channel depth.

9. (Original) A field effect transistor as recited in claim 1, wherein said discontinuous film is an insulator including a portion formed of oxidized SiGe, wherein said discontinuity defines a location of a conductor connected to a channel of said field effect transistor.

10. (Currently Amended) ~~A field effect transistor as recited in claim 1, further including~~ A field effect transistor formed at a surface of a layer of semiconductor material, said field effect transistor comprising

a gate structure formed on said surface of said layer of semiconductor material,

a discontinuous film of material within said layer of semiconductor material and having a discontinuity aligned to said gate structure, and

a void within said layer of semiconductor material.

11. (Currently amended) An integrated circuit including a field effect transistor formed at a surface of a layer of semiconductor material, said field effect transistor comprising

a gate structure formed on said surface of said layer of semiconductor material, ~~and~~

a discontinuous film of material within said layer of semiconductor material and having a discontinuity aligned to said gate structure, and

a void within said layer of semiconductor material.

12. (Original) An integrated circuit as recited in claim 11, wherein said discontinuous film has a stepped or staircase profile in cross-section.

13. (Previously presented) An integrated circuit as recited in claim 12 wherein said stepped or staircase portion defines an effective channel depth.

14. (Original) An integrated circuit as recited in claim 11, wherein said discontinuous film is an insulator including a portion formed of oxidized SiGe, wherein said discontinuity defines a location of a conductor connected to a channel of said field effect transistor.

15. - 20. (Canceled)

21. (Currently Amended) A field effect transistor formed at a surface of a layer of semiconductor material, said field effect transistor comprising

a gate structure formed on said surface of said layer of semiconductor material, and

a discontinuous film of material within said layer of semiconductor material at a predetermined distance from said surface of said layer of semiconductor material wherein said discontinuous film is a stressed film, said discontinuous film having a discontinuity which includes an edge which is located in a position defined by an edge said gate structure,

said discontinuity defining a structure for performing at least one of:

defining a depth of a conduction channel of said field effect transistor within said layer of semiconductor material to less than said predetermined distance from said surface of said semiconductor material; and

applying stress to said conduction channel of said field effect transistor.

22. (Previously Presented) A field effect transistor as recited in claim 21, wherein said discontinuity is self-aligned to said gate structure.

23. (Canceled)

24. (Currently Amended) A field effect transistor as recited in claim ~~23~~ 21, wherein said stressed film comprises an insulator.

25. (Canceled)